



RESPONSE UNDER 37 C.F.R. 1.116-
EXPEDITED PROCEDURE
EXAMINING GROUP 1765
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#15/D
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TC 1700

Appl. No. : 09/464,297
Applicants: : Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball, Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib
Filed: : December 15, 1999
Title : PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND AN RF BIAS APPLIED TO THE SUBSTRATE
Grp./ A.U. : 1765
Examiner : Lan Vinh
Docket No. : 99-039

CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450	
on	<u>July 24, 2003</u> (Date of Deposit)
John P. Taylor, Reg. No. 22,369	
	<u>John P. Taylor</u> Signature
	<u>July 24, 2003</u> Date of Signature

RESPONSE TO FINAL REJECTION

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: July 24, 2003

Sir:

In response to the Final Rejection (Fifth Office Action) mailed June 4, 2003, please amend the application as follows: